



### 60V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET

## **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> T <sub>C</sub> = +25°C
60V	$6m\Omega @ V_{GS} = 10V$	100A
60 V	$10m\Omega @ V_{GS} = 4.5V$	85A

## **Description and Applications**

This new generation MOSFET features low on-resistance and fast switching, making it ideal for high efficiency power management applications.

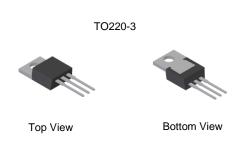
- Engine Management Systems
- Body Control Electronics
- DC-DC Converters

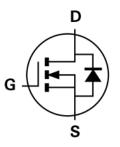
### **Features**

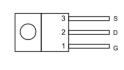
- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching Ensures more Reliable and Robust End Application
- Low Input Capacitance
- Low Input/Output Leakage
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

### **Mechanical Data**

- Case: TO220-3
- Case Material: Molded Plastic, "Green" Molding Compound, UL Flammability Classification Rating 94V-0
- Terminals: Matte Tin Finish annealed over Copper leadframe.
   Solderable per MIL-STD-202, Method 208 ®3
- Terminal Connections: See Diagram Below
- Weight: 1.85 grams (Approximate)







**Equivalent Circuit** 

Top View Pin Out Configuration

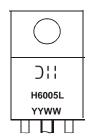
### Ordering Information (Note 4)

Part Number	Case	Packaging
DMTH6005LCT	TO220-3	50 Pieces/Tube

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**



D::I=Manufacturer's Marking
H6005L = Product Type Marking Code
YYWW = Date Code Marking
YY or YY = Last Two Digits of Year (ex: 16 = 2016)
WW or WW = Week Code (01 to 53)



## **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	$V_{DSS}$	60	V	
Gate-Source Voltage	$V_{GSS}$	±20	V	
Continuous Prain Current (Note 6)	T <sub>C</sub> = +25°C	I <sub>D</sub>	100	А
Continuous Drain Current (Note 6)	T <sub>C</sub> = +100°C		78	
Maximum Continuous Body Diode Forward Current (Note 6)	T <sub>C</sub> = +25°C	Is	100	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	160	Α	
Avalanche Current, L=1mH	I <sub>AS</sub>	14.8	Α	
Avalanche Energy, L=1mH	E <sub>AS</sub>	98	mJ	

## **Thermal Characteristics**

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	$T_A = +25^{\circ}C$	$P_{D}$	2.8	W
Thermal Resistance, Junction to Ambient (Note 5)		$R_{\theta JA}$	52.8	°C/W
Total Power Dissipation (Note 6)	$T_C = +25^{\circ}C$	$P_{D}$	125	W
Thermal Resistance, Junction to Case (Note 6)		$R_{\theta JC}$	1.2	°C/W
Operating and Storage Temperature Range		$T_{J,}T_{STG}$	-55 to +175	°C

## **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

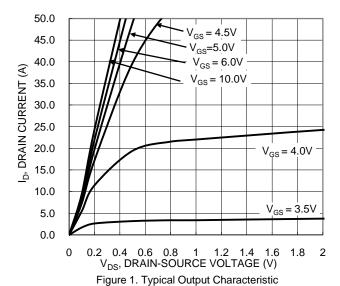
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Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)	, ,		1			<u> </u>	
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	_	_	V	$V_{GS} = 0V$ , $I_D = 1mA$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	1	μΑ	$V_{DS} = 48V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_		±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1	_	3	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance		ı	4.5	6	mΩ	$V_{GS} = 10V, I_D = 20A$	
Static Diani-Source Off-Resistance	R <sub>DS(ON)</sub>	-	8.8	10	mΩ	$V_{GS} = 4.5V, I_D = 12.5A$	
Diode Forward Voltage	$V_{SD}$	_	_	1.2	V	$V_{GS} = 0V, I_{S} = 20A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C <sub>iss</sub>	1	2962	_		$V_{DS} = 30V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Output Capacitance	Coss	ı	965.2	_	pF		
Reverse Transfer Capacitance	C <sub>rss</sub>	-	59.8	_			
Gate Resistance	$R_{g}$	1	0.66	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = 10V)	$Q_g$	_	47.1	_			
Total Gate Charge (V <sub>GS</sub> = 4.5V)	$Q_{g}$	1	23.1	_	nC	$V_{DD} = 30V, I_D = 50A$	
Gate-Source Charge	$Q_{gs}$	-	10.2	_	IIC		
Gate-Drain Charge	$Q_{gd}$	_	12.5	_			
Turn-On Delay Time	t <sub>D(ON)</sub>	_	8.3	_		V <sub>DD</sub> = 30V, V <sub>GS</sub> = 10V,	
Turn-On Rise Time	t <sub>R</sub>	_	9.4	_			
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	22	_	ns	$I_D = 30A, R_g = 3.3\Omega$	
Turn-Off Fall Time	t <sub>F</sub>	_	8.9	_		_	
Reverse Recovery Time	t <sub>RR</sub>	_	40.4	_	ns	I_ 204 di/dt 1004/up	
Reverse Recovery Charge	$Q_{RR}$	_	49.7	_	nC		

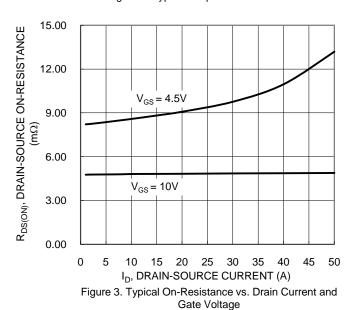
5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.

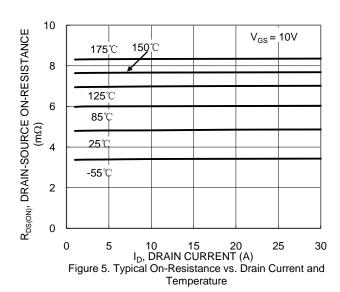
- 6. Device mounted on infinite heat sink.
- 7. Short duration pulse test used to minimize self-heating effect.
  8. Guaranteed by design. Not subject to product testing.

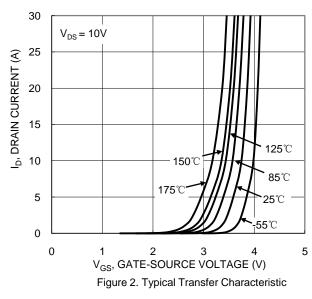


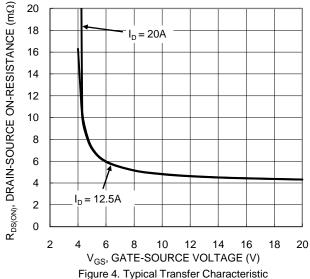


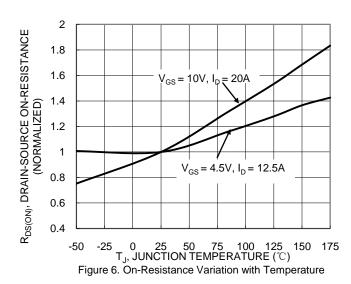




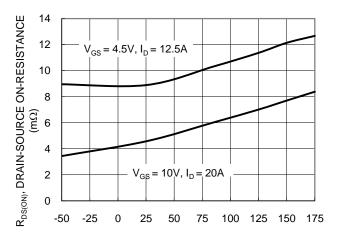












 $T_J, JUNCTION TEMPERATURE (^{\mathbb{C}})$  Figure 7. On-Resistance Variation with Temperature

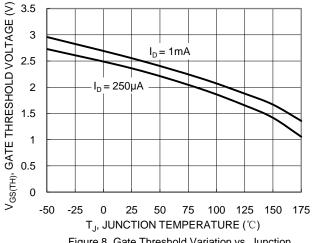
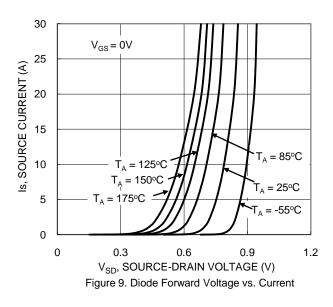
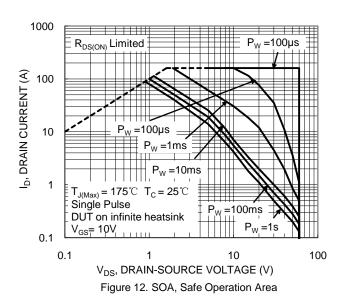


Figure 8. Gate Threshold Variation vs. Junction Temperature

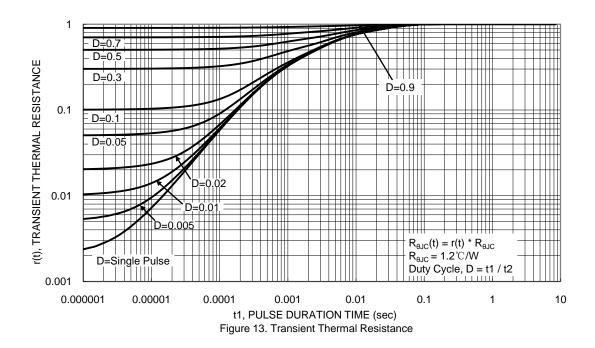


 $V_{GS}(V)$  $V_{DS} = 30V, I_{D} = 50A$ Qg (nC)

f=1MHz Ciss C<sub>T</sub>, JUNCTION CAPACITANCE (pF)  $C_{oss}$ V<sub>DS</sub>, DRAIN-SOURCE VOLTAGE (V) Figure 10. Typical Junction Capacitance



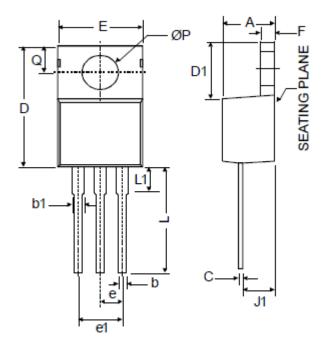




## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO220-3



TO220-3				
Dim	Min	Max		
Α	3.55	4.85		
b	0.51	1.14		
b1	1.14	1.78		
С	0.31	1.14		
D	14.20	16.50		
D1	5.84	6.86		
Е	9.70	10.70		
е	2.79	2.99		
e1	4.83	5.33		
F	0.51	1.40		
J1	2.03	2.92		
L	12.72	14.72		
L1	3.66	6.35		
Р	3.53	4.09		
Q	2.54	3.43		
All Dimensions in mm				



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